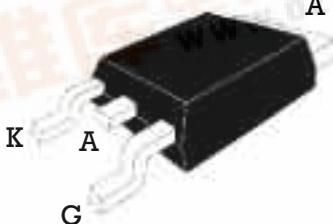




FS04...D

SURFACE MOUNT SCR

DPAK (Plastic) 	On-State Current 4 Amp	Gate Trigger Current $< 200 \mu\text{A}$
	Off-State Voltage 200 V ÷ 600 V	
<p>These series of Silicon Controlled Rectifier use a high performance PNPN technology.</p> <p>These parts are intended for general purpose applications where high gate sensitivity is required using surface mount technology.</p>		

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Min.	Max.	Unit
$I_{T(\text{RMS})}$	On-state Current	180° Conduction Angle, $T_c = 115^\circ\text{C}$	4	10	A
$I_{T(\text{AV})}$	Average On-State Current	Half Cycle, $\theta = 180^\circ$, $T_c = 115^\circ\text{C}$	2.5	5	A
I_{TSM}	Non-repetitive On-State Current	Half Cycle, 60 Hz	33	50	A
I_{TSM}	Non-repetitive On-State Current	Half Cycle, 50 Hz	30	40	A
I^2t	Fusing Current	$t = 10 \text{ ms}$, Half Cycle	4.5	10	A^2s
V_{GRM}	Peak Reverse Gate Voltage	$I_{\text{GR}} = 10 \mu\text{A}$	8	15	V
I_{GM}	Peak Gate Current	20 μs max.		1.2	A
P_{GM}	Peak Gate Dissipation	20 μs max.		3	W
$P_{G(\text{AV})}$	Gate Dissipation	20 ms max.		0.2	W
T_j	Operating Temperature		-40	+125	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40	+150	$^\circ\text{C}$
T_{sld}	Soldering Temperature	10s max		260	$^\circ\text{C}$

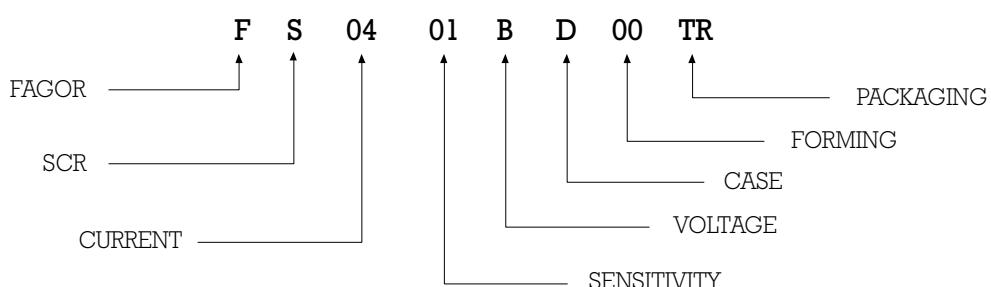
SYMBOL	PARAMETER	CONDITIONS	VOLTAGE			Unit
			B	D	M	
V_{DRM}	Repetitive Peak Off State Voltage	$R_{\text{GK}} = 1 \text{ k}\Omega$	200	400	600	V
V_{RRM}						

SURFACE MOUNT SCR

Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	SENSITIVITY				Unit	
			01	04	02	03		
I_{GT}	Gate Trigger Current	$V_D = 12 \text{ V}_{DC}$, $R_L = 33 \Omega$, $T_j = 25^\circ\text{C}$	MIN MAX	1 20	15 50	200	200	μA
I_{DRM} / I_{RRM}	Off-State Leakage Current	$V_D = V_{DRM}$, $R_{GK} = 220 \Omega$, $T_j = 125^\circ\text{C}$ $V_R = V_{RRM}$, $T_j = 25^\circ\text{C}$	MAX MAX		1 5			mA μA
V_{TM}	On-state Voltage	at $I_T = 8 \text{ Amp}$, $t_p = 380 \mu\text{s}$, $T_j = 25^\circ\text{C}$	MAX		1.6			V
V_{GT}	Gate Trigger Voltage	$V_D = 12 \text{ V}_{DC}$, $R_L = 33 \Omega$, $T_j = 25^\circ\text{C}$	MAX		0.8			V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}$, $R_L = 3.3 \text{ K}\Omega$, $R_{GK} = 220 \Omega$, $T_j = 125^\circ\text{C}$	MIN		0.1			V
I_H	Holding Current	$I_T = 50 \text{ mA}$, $R_{GK} = 1\text{K}\Omega$, $T_j = 25^\circ\text{C}$	MAX		5			mA
I_L	Latching Current	$I_G = 1 \text{ mA}$, $R_{GK} = 1\text{K}\Omega$, $T_j = 25^\circ\text{C}$	MAX		6			mA
dv / dt	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}$, $R_{GK} = 220 \Omega$, $T_j = 125^\circ\text{C}$	MIN	10	10	5	10	$\text{V}/\mu\text{s}$
di / dt	Critical Rate of Current Rise	$I_G = 2 \times I_{GT}$, $t_r = 100 \text{ ns}$, $F = 60 \text{ Hz}$, $T_j = 125^\circ\text{C}$	MIN		50			$\text{A}/\mu\text{s}$
$R_{th(j-c)}$	Thermal Resistance Junction-Case for DC				3			$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	Thermal Resistance Junction-Amb (S=0.5 cm ²)				70			$^\circ\text{C}/\text{W}$

PART NUMBER INFORMATION



SURFACE MOUNT SCR

Fig. 1: Maximum average power dissipation versus average on-state current

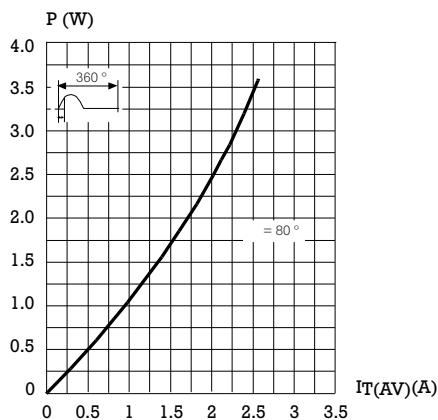


Fig. 3: Average and DC on-state current versus ambient temperature (device mounted on FR4 with recommended pad layout)

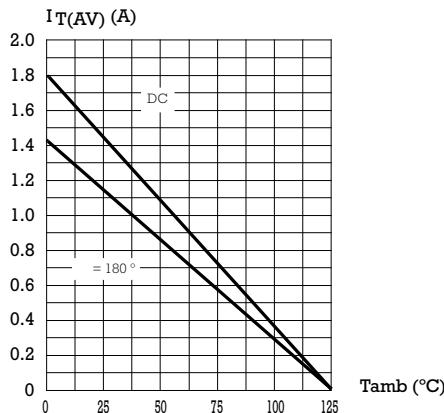


Fig. 4-2: Relative variation of thermal impedance junction to ambient versus pulse duration. (recommended pad layout)

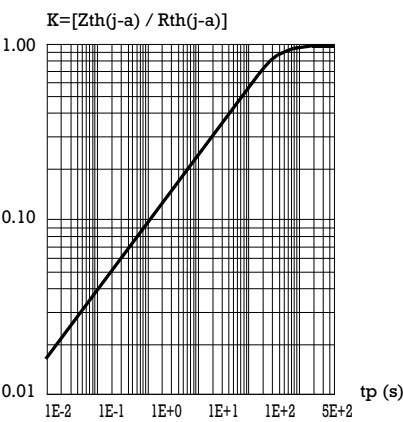


Fig. 2: Correlation between maximum average power dissipation and maximum allowable temperatures (Tamb and T case) for different thermal resistances heatsink+contact.

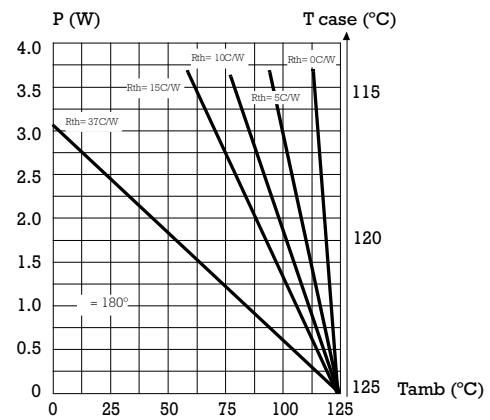


Fig. 4-1: Relative variation of thermal impedance junction to case versus pulse duration.

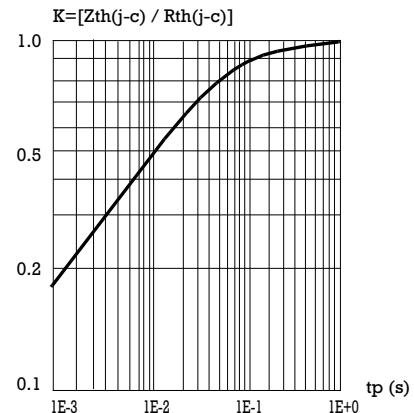
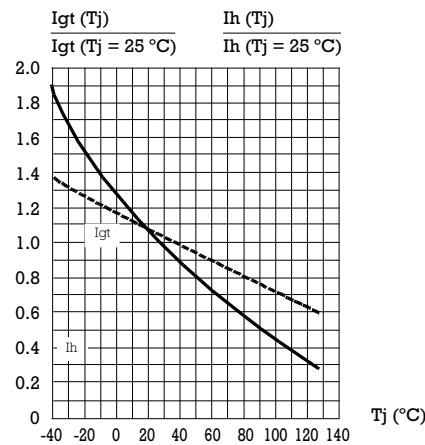


Fig. 5: Relative variation of gate trigger current and holding current versus junction temperature.



SURFACE MOUNT SCR

Fig. 6: Non repetitive surge peak on-state current versus number of cycles.

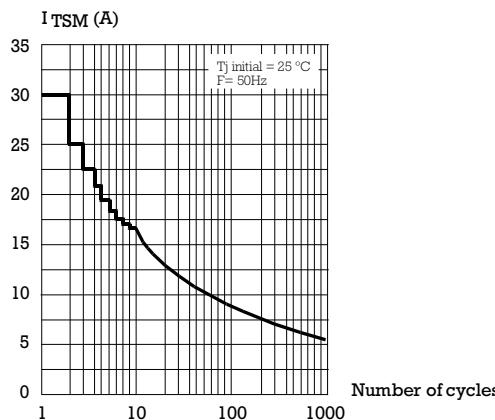


Fig. 8: On-state characteristics (maximum values).

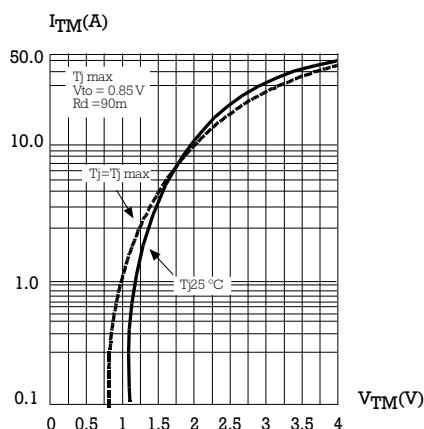


Fig. 10: Typical reflow soldering heat profile, either for mounting on FR4 or metal-backed boards.

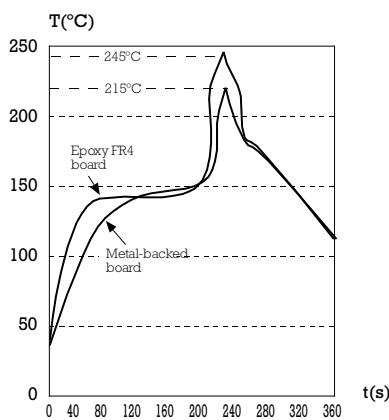


Fig. 7: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t_p < 10\text{ ms}$, and corresponding value of I^2t .

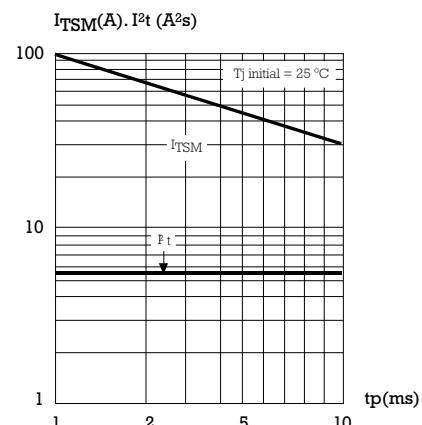
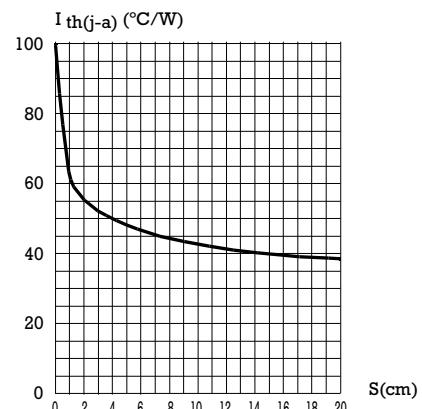
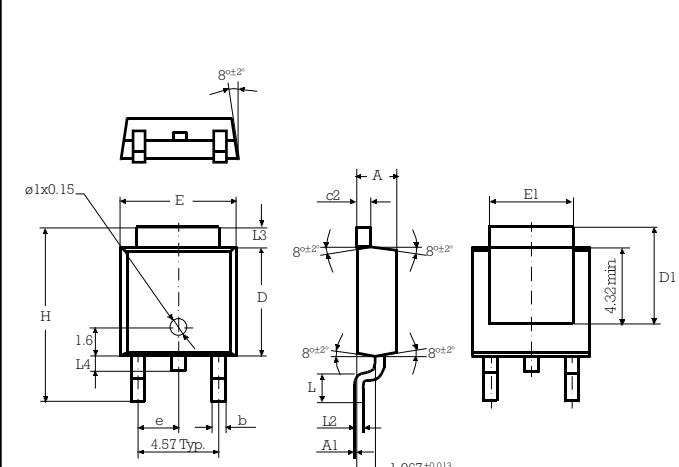


Fig. 9: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35μm).



SURFACE MOUNT SCR

PACKAGE MECHANICAL DATA DPAK TO 252-AA



REF.	DIMENSIONS		
	Milimeters		
	Min.	Nominal	Max.
A	2.18	2.3±0.18	2.39
A1	0	0.12	0.127
b	0.64	0.75±0.1	0.89
c	0.46		0.61
c1	0.46		0.56
c2		0.8±0.013	
D	5.97	6.1±0.1	6.22
D1	5.21		5.52
E	6.35	6.58±0.14	6.73
E1	5.20	5.36±0.1	5.46
e		2.28BSC	
H	9.40	9.90±0.15	10.41
L	1.40		1.78
L1	2.55	2.6±0.05	2.74
L2	0.46	0.5±0.013	0.58
L3	0.89	1.20±0.05	1.27
L4	0.64	0.83±0.1	1.02

Marking: type number
Weight: 0.2 g

FOOT PRINT

